

Specifications	
Part Number	FQP32N20C_F080
Manufacturer	Fairchild/ON Semiconductor
Description	MOSFET N-CH 200V 28A TO-220
Category	Discrete Semiconductor Products > Transistors - FETs,
Part Status	2606 pcs Stock
Vgs(th) (Max) @ Id	4V @ 250μA
Technology	MOSFET (Metal Oxide)
Supplier Device Package	TO-220AB
Series	QFET®
Rds On (Max) @ Id, Vgs	82 mOhm @ 14A, 10V
Power Dissipation (Max)	156W (Tc)
Packaging	Tube
Package / Case	TO-220-3
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Through Hole
Input Capacitance (Ciss) (Max) @ Vds	2200pF @ 25V
Gate Charge (Qg) (Max) @ Vgs	110nC @ 10V
FET Type	N-Channel
FET Feature	-
Drain to Source Voltage (Vdss)	200V
Current - Continuous Drain (Id) @ 25°C	28A (Tc)

In:

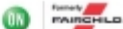
ON Semiconductor

FQP33N10
AMI Semiconductor / ON
Semiconductor
MOSFET N-CH 100V 33A TO-220

ON Semiconductor® 

FQP32N12V2
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MOSFET N-CH 120V 32A TO-220

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MOSFET N-CH 200V 28A TO-220

FQP32N12V2 MOS
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More

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